L Number	Hits	Search Text	DB	Time stamp
	182	(interdigitate or interdigitated or	USPAT;	2004/11/01
13	102	interdigitate or interdigitated or interdigitating) and (scr or (silicon near	US-PGPUB;	
		(control or controlling or controlled)))	EPO; JPO;	07:59
		(control of controlling of controlled)))	DERWENT;	
			IBM_TDB	
	0	(interdigitate or interdigitated or	USPAT;	2004/11/01
14		interdigitating) and (scr or (silicon near	US-PGPUB;	08:00
		(control or controlling or controlled))) and	EPO; JPO;	00:00
		salling	DERWENT;	
		Janning	IBM_TDB	· .
15	15	(interdigitate or interdigitated or	USPAT;	2004/11/01
	13	interdigitating) and (scr or (silicon near	US-PGPUB;	08:00
		(control or controlling or controlled))) and	EPO; JPO;	00:00
		duvvury	DERWENT;	
		duvvary	IBM_TDB	
16	2	(interdigitate or interdigitated or	USPAT;	2004/11/01
16	_	interdigitation).ti,ab,clm. and (scr or	US-PGPUB;	08:01
		(silicon near (control or controlling or	EPO; JPO;	00:01
		controlled))) and duvvury	DERWENT;	
		controlled/// and duvvury	IBM_TDB	
17	32	(interdigitate or interdigitated or	USPAT;	2004/11/01
•	32	interdigitating).ti,ab,clm. and (scr or	US-PGPUB;	08:01
		(silicon near (control or controlling or	EPO; JPO;	00:01
•		controlled)))	DERWENT;	
			IBM_TDB	
18	5	(interdigitate or interdigitated or	USPAT;	2004/11/01
	Ŭ	interdigitating).ti,ab,clm. and (scr or	US-PGPUB;	08:03
		(silicon near (control or controlling or	EPO; JPO;	00.03
		controlled))).ti,ab,clm.	DERWENT;	
İ			IBM_TDB	
19	3	(interdigitate or interdigitated or	USPAT;	2004/11/01
·		interdigitating).ti,ab,clm. and (scr or	US-PGPUB;	08:03
		(silicon near (control or controlling or	EPO; JPO;	30.00
		controlled))).ti,ab,clm. and diode and anode	DERWENT;	
		and cathode	IBM_TDB	
20	0	(interdigitate or interdigitated or	USPAT;	2004/11/01
ĺ	_	interdigitating).ti,ab,clm. and (scr or	US-PGPUB;	08:05
		(silicon near (control or controlling or	EPO; JPO;	
		controlled))).ti,ab,clm. and diode and anode	DERWENT;	
		and cathode and (low near voltage)	IBM_TDB	
21	76	(interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation) and (scr or	US-PGPUB;	08:06
		(silicon near (control or controlling or	EPO; JPO;	
		controlled))) and diode and anode and	DERWENT;	
		cathode	IBM_TDB	
22	24	(interdigitate or interdigitating or	USPAT;	2004/11/01
İ	-	interdigitated or interdigitation) and (scr or	US-PGPUB;	08:06
		(silicon near (control or controlling or	EPO; JPO;	.
		controlled))) and diode and anode and	DERWENT;	
		cathode and (electrostatic or esd)	IBM_TDB	

23	19	(interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation) and (scr or	US-PGPUB;	08:07
		(silicon near (control or controlling or	EPO; JPO;	
		controlled))) and diode and anode and	DERWENT;	
		cathode and (electrostatic or esd).ti,ab,clm.	IBM_TDB	
24	0	((interdigitate or interdigitating or	USPAT;	2004/11/01
İ		interdigitated or interdigitation) and (scr or	US-PGPUB;	08:07
		(silicon near (control or controlling or	EPO; JPO;	
		controlled))) and diode and anode and	DERWENT;	
		cathode and (electrostatic or	IBM_TDB	
		esd).ti,ab,clm.) and (low near current)		
25	12	((interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation) and (scr or	US-PGPUB;	08:08
		(silicon near (control or controlling or	EPO; JPO;	
		controlled))) and diode and anode and	DERWENT;	
		cathode and (electrostatic or	IBM_TDB	
		esd).ti,ab,clm.) and (esd near10 current)	_	
26	5	((interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation) and (scr or	US-PGPUB;	08:08
		(silicon near (control or controlling or	EPO; JPO;	
		controlled))) and diode and anode and	DERWENT;	
ŀ		cathode and (electrostatic or	IBM_TDB	
		esd).ti,ab,clm.) and (esd near5 low near5	_	
		voltage)		
27	5	((interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation) and (scr or	US-PGPUB;	08:08
		(silicon near (control or controlling or	EPO; JPO;	
		controlled))) and diode and anode and	DERWENT;	
		cathode and (electrostatic or	IBM_TDB	
		esd).ti,ab,clm.) and (esd near5 low near		
		voltage)		
28	0	((interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation) and (scr or	US-PGPUB;	08:08
		(silicon near (control or controlling or	EPO; JPO;	
		controlled))) and diode and anode and	DERWENT;	
		cathode and (electrostatic or	IBM_TDB	
		esd).ti,ab,clm.) and (esd near5 low near		
		voltage).ti,ab,clm.		
29	9	((interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation) and (scr or	US-PGPUB;	08:11
		(silicon near (control or controlling or	EPO; JPO;	
		controlled))) and diode and anode and	DERWENT;	
		cathode) and 257/360	IBM_TDB	
30	40	(interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation) and (multi	US-PGPUB;	08:14
		near finger)	EPO; JPO;	
			DERWENT;	ĺ
!			IBM_TDB	
31	3	(interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation) and (multi	US-PGPUB;	08:15
		near finger) and scr	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

32	3	(interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation) and (multi	US-PGPUB;	08:15
		near finger) and scr and diode	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
33	0	(interdigitate or interdigitating or	USPAT;	2004/11/01
		interdigitated or interdigitation).clm. and	US-PGPUB;	08:16
		(multi near finger) and scr and diode and	EPO; JPO;	
		anode and cathode	DERWENT;	:
			IBM_TDB	
34	15	salling and duvvury	USPAT;	2004/11/01
			US-PGPUB;	08:16
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	